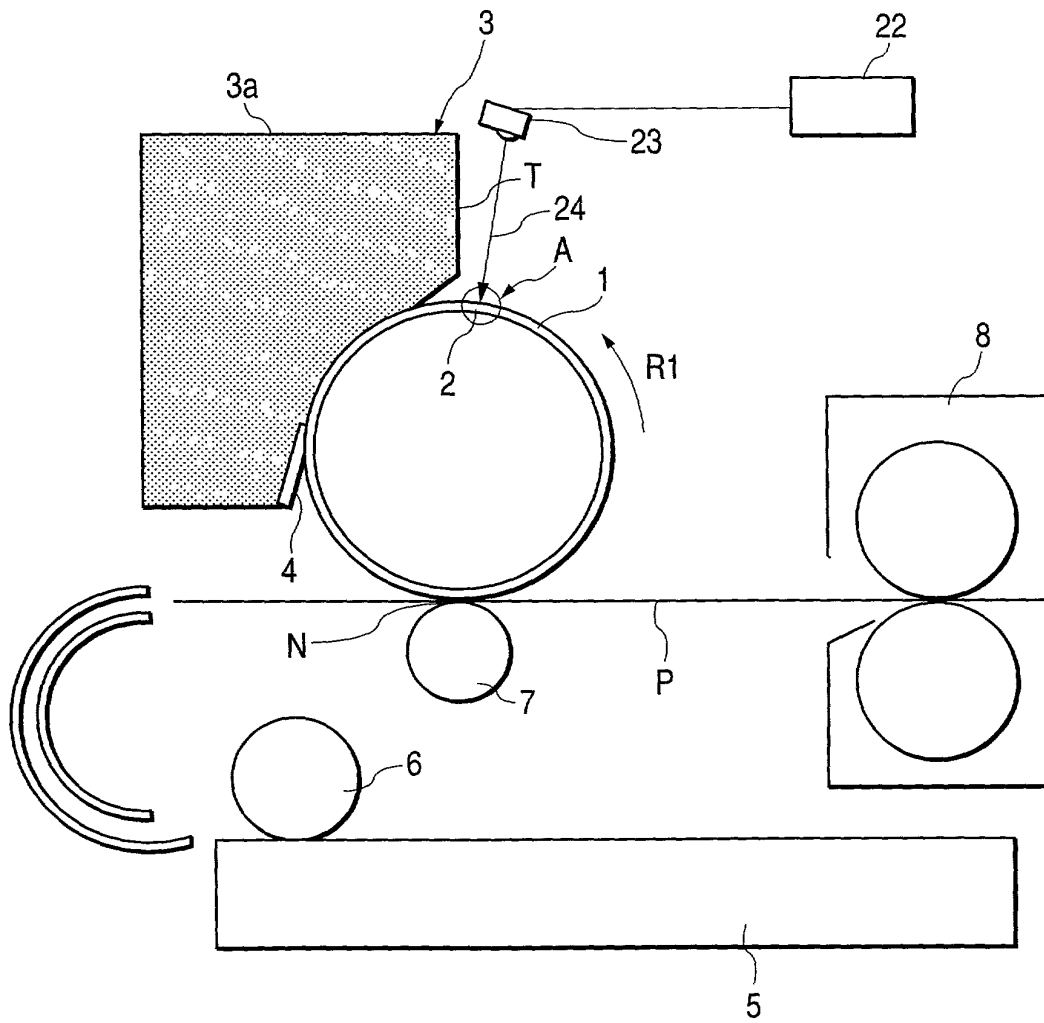


FIG. 1



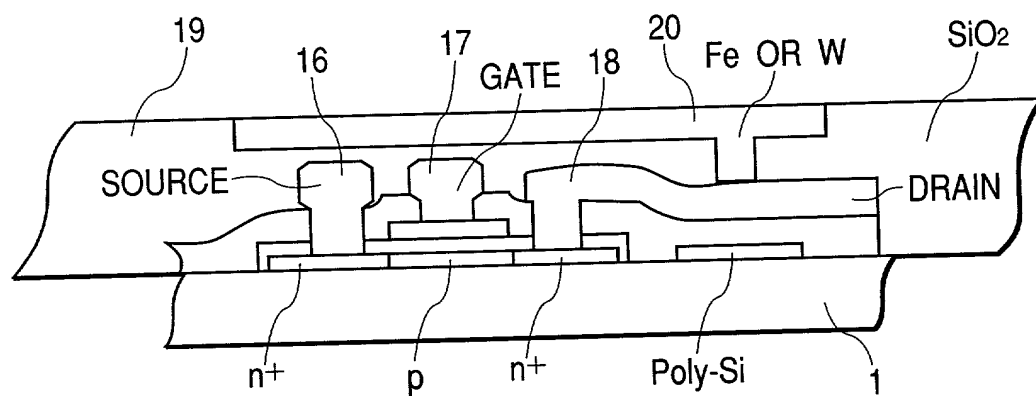
**FIG. 2**

Fig. 1 is a perspective view of a cylindrical member 1. The member 1 is composed of a core 11 and an outer layer 1a. The core 11 is labeled "a-Si".

A cross-sectional view of a semiconductor device. It shows a substrate 1 with a gate insulating film 12 and a gate electrode 13. A poly-silicon layer Poly-Si is formed on the gate insulating film 12.

FIG. 4

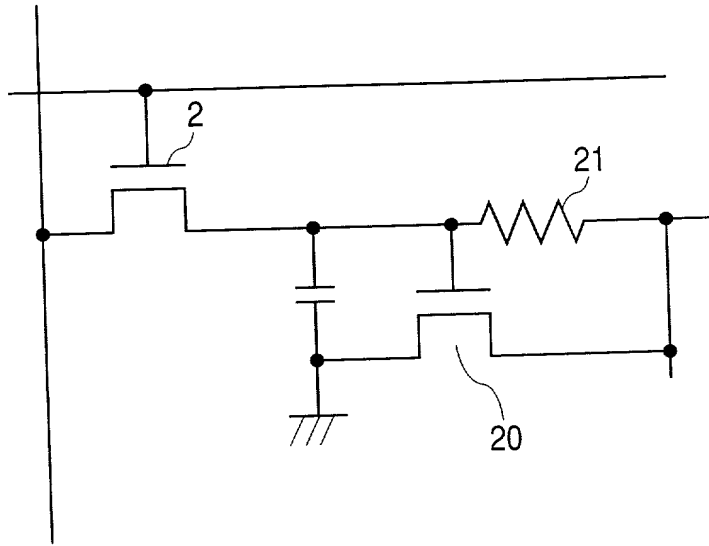


FIG. 5

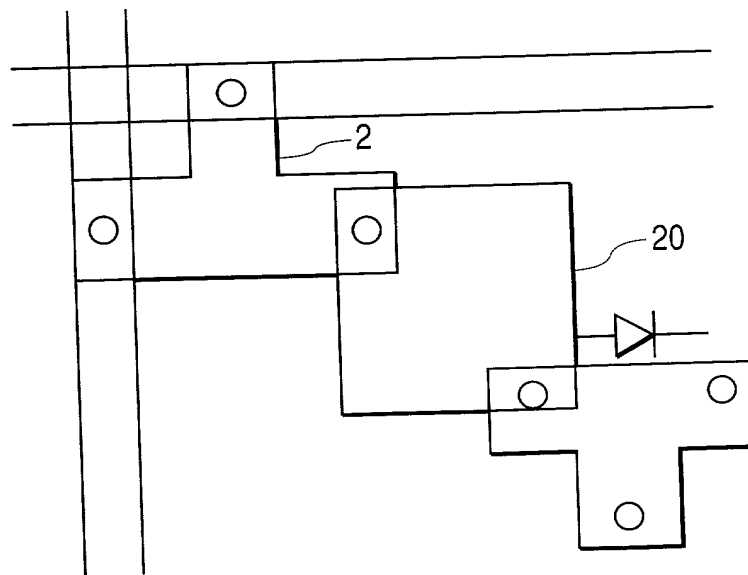
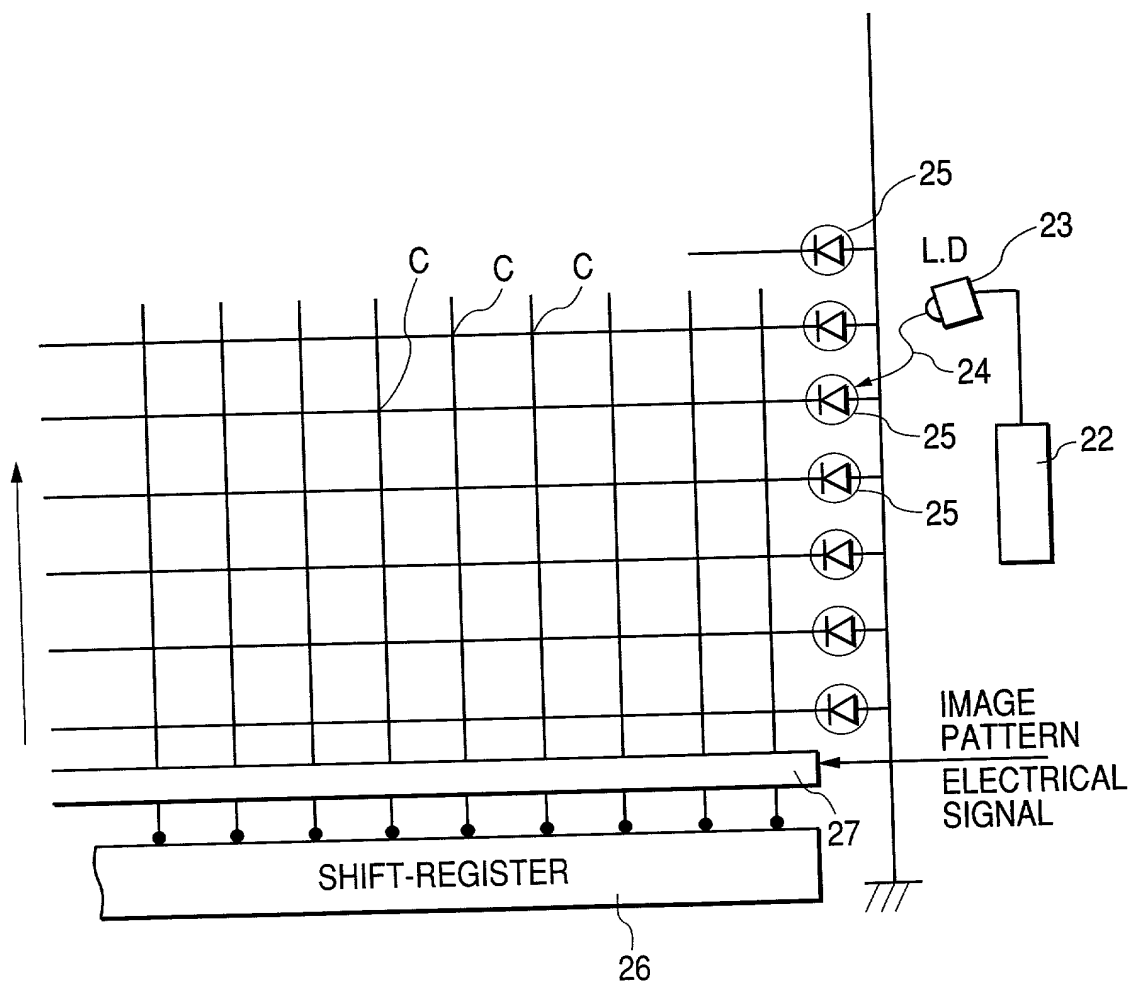


FIG. 6



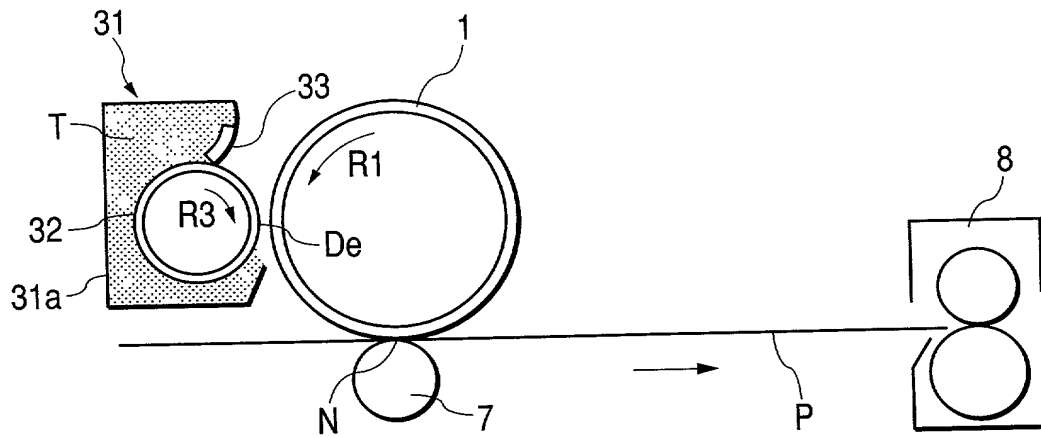
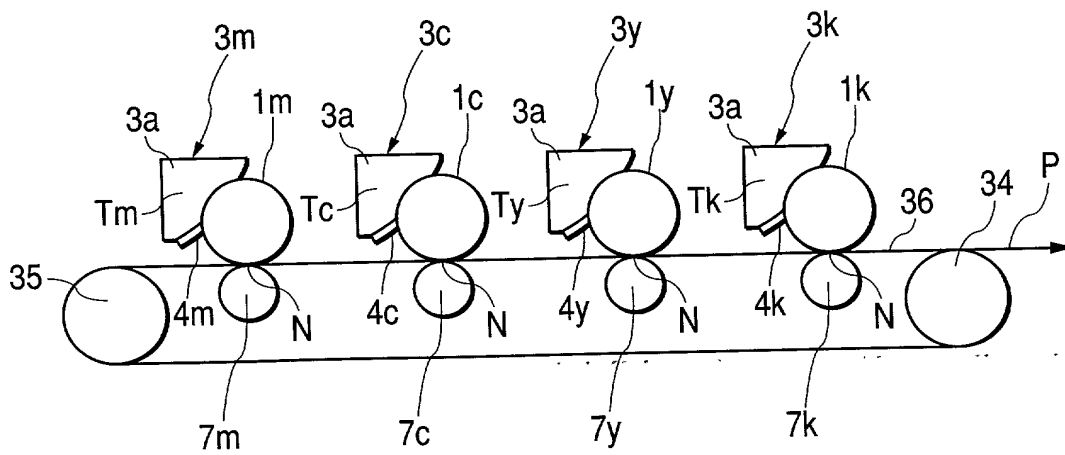
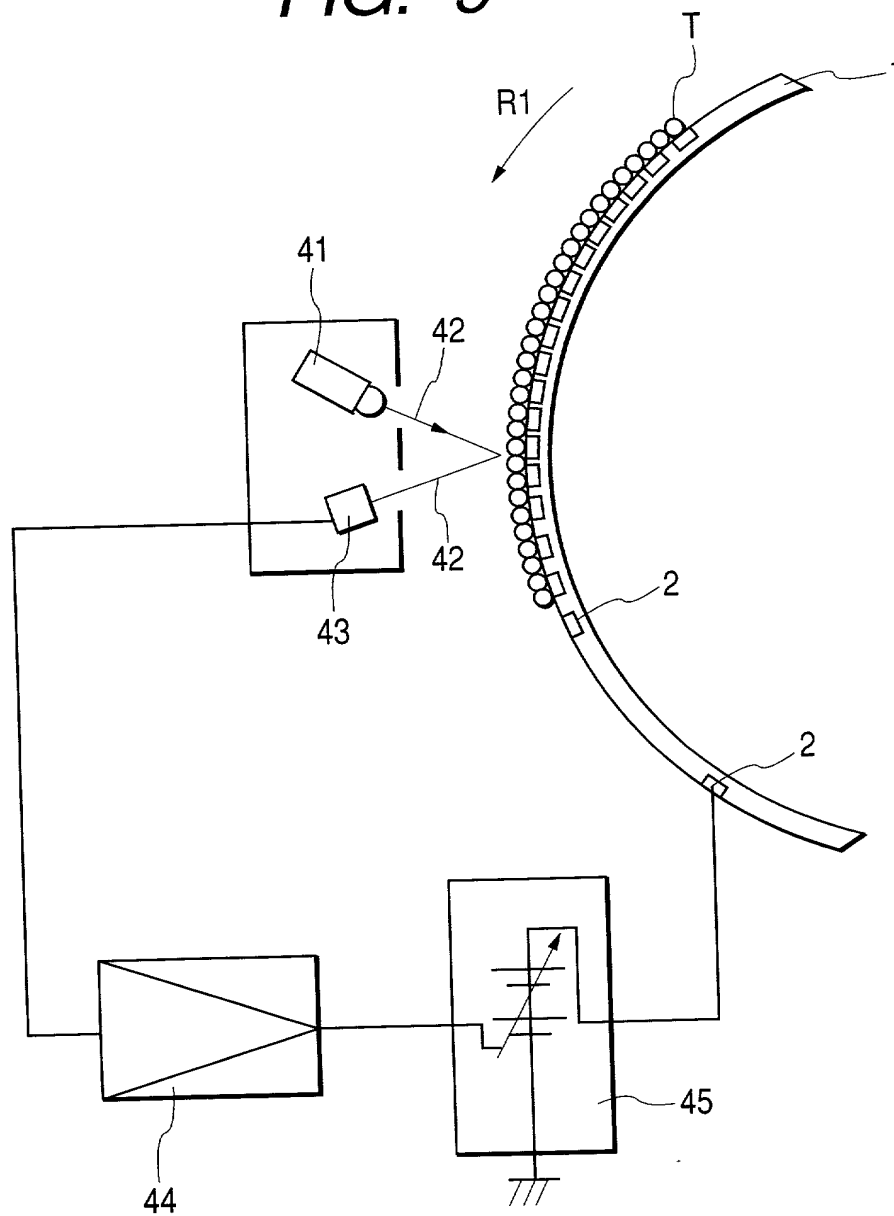
**FIG. 7****FIG. 8**

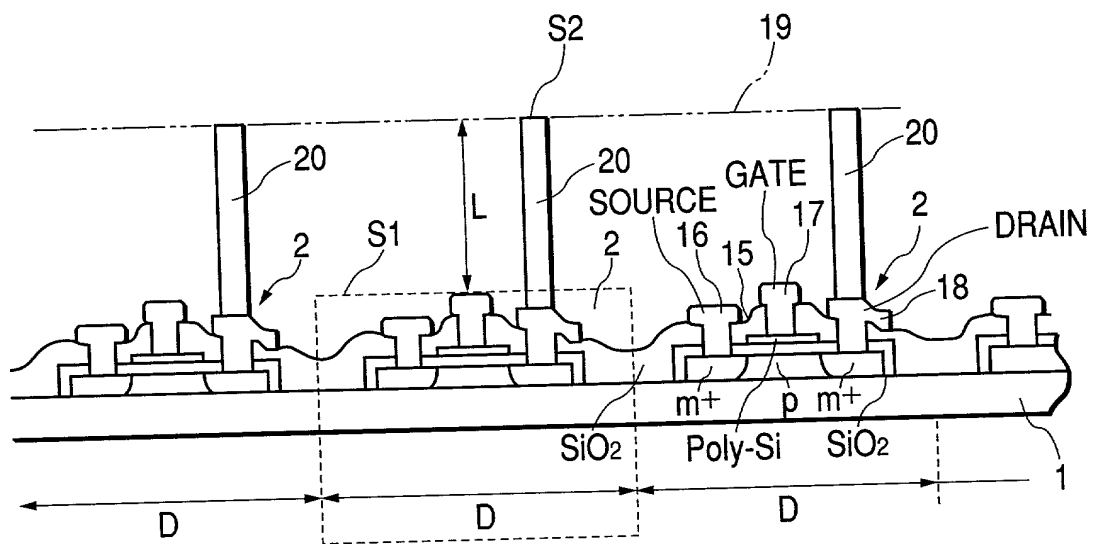
FIG. 9

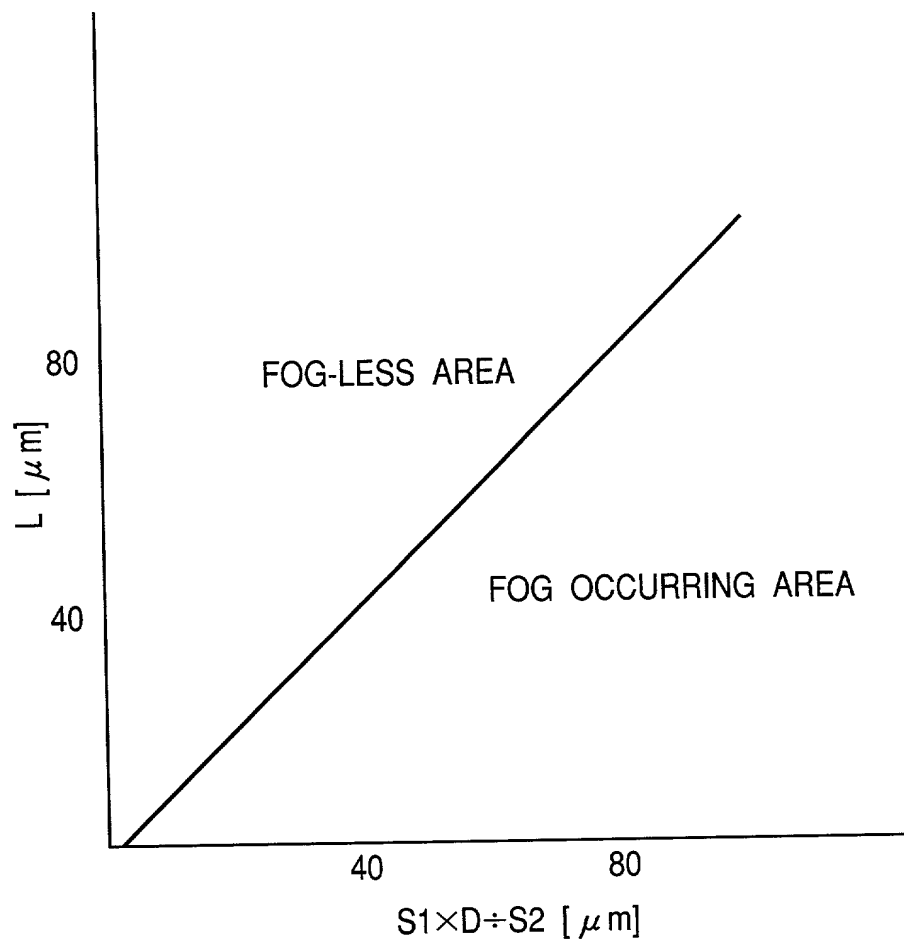
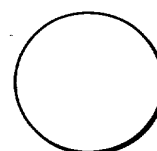
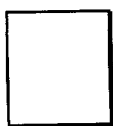


**FIG. 11**

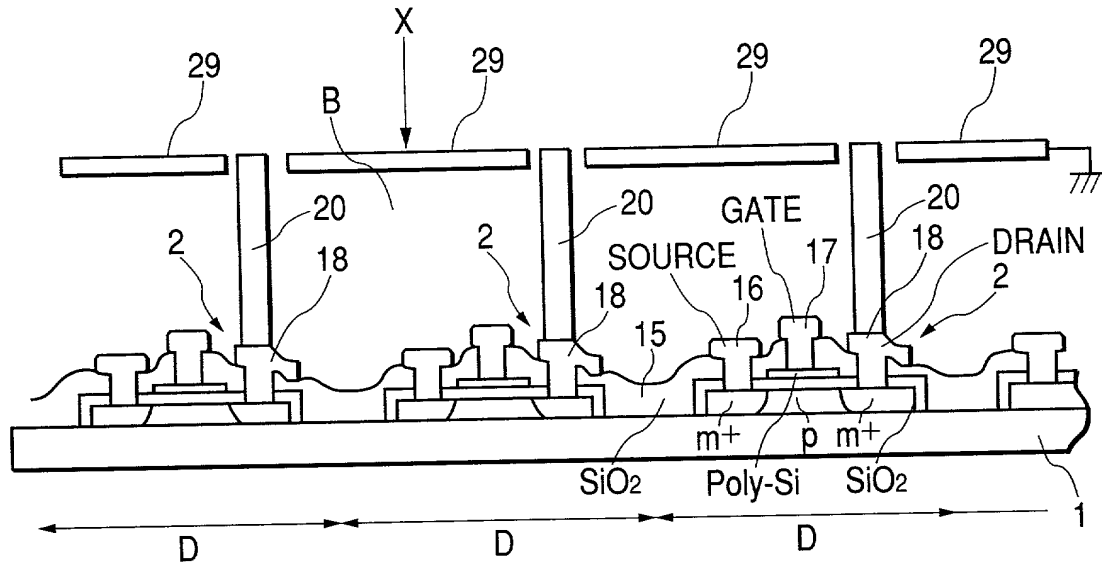


FIG. 12



**FIG. 13****FIG.14A FIG.14B FIG.14C FIG.14D**

**FIG. 15A**



**FIG. 15B**

